

Silicon PNP Power Transistor

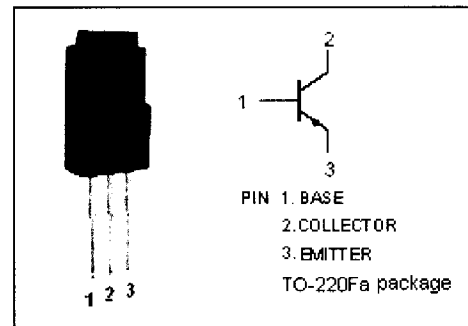
2SA1304

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
 $V_{(BR)CEO} = -150V(\text{Min})$
- Complement to Type 2SC3296

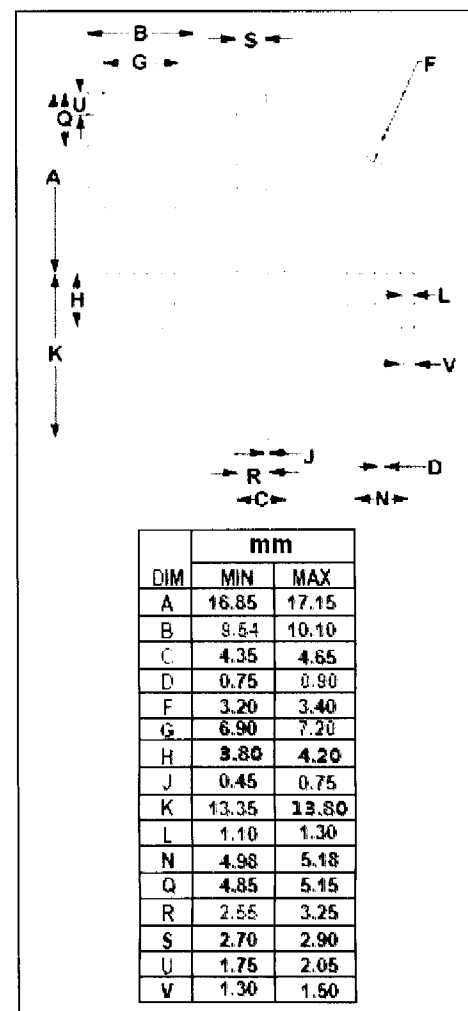
APPLICATIONS

- Power amplifier applications.
- Vertical output applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1.5	A
I_B	Base Current-Continuous	-0.5	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	20	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA; I _B = 0	-150			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -0.5A; I _B = -50mA			-1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -0.5A; V _{CE} = -10V			-0.85	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -120V; I _E = 0			-10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-10	μ A
h _{FE}	DC Current Gain	I _C = -0.5A; V _{CE} = -10V	40		140	
f _T	Current-Gain—Bandwidth Product	I _C = -0.5A; V _{CE} = -10V		4		MHz
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f= 1MHz		55		pF